



175°C 60V DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _A = +25°C
001/	$48mΩ @ V_{GS} = -10V$	-5.2A
-60V	$60m\Omega$ @ $V_{GS} = -4.5V$	-4.7A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

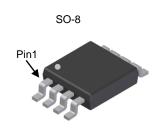
- Engine Management Systems
- **Body Control Electronics**
- **DC-DC Converters**

Features

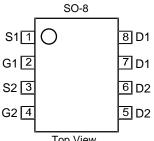
- Rated to +175°C ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low R_{DS(ON)} minimises power losses
- Low Qg minimises switching losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMPH6050SSDQ)

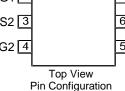
Mechanical Data

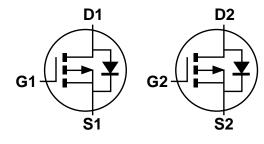
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.076 grams (Approximate)



Top View







Equivalent Circuit

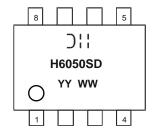
Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH6050SSD-13	SO-8	2500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃!! = Manufacturer's Marking H6050SD = Product Type Marking Code YYWW = Date Code Marking YY or \overline{YY} = Year (ex: 16 = 2016) WW = Week (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) $V_{GS} = -10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +100^{\circ}C$		I _D	-5.2 -3.7	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-35	Α
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-2.0	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-25	Α
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	33	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

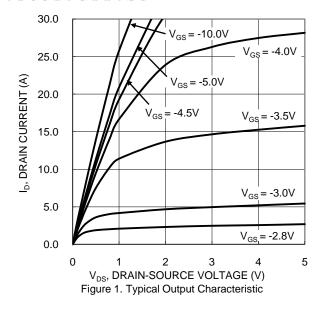
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	D	103	°C/W
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	$R_{\theta JA}$	64	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	75	°C/W
Thermal Resistance, Junction to Ambient (Note o)	t<10s	$R_{\theta JA}$	47	
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	13	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I_{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0		-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			34	48	mΩ	$V_{GS} = -10V, I_D = -5A$	
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	44	60		$V_{GS} = -4.5V, I_D = -4A$	
Diode Forward Voltage	V_{SD}		-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	1525	_	pF	\/ 20\/ \/ 0\/	
Output Capacitance	Coss	_	90	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	70	_	pF	1 = 1.0WHZ	
Gate Resistance	R_{g}		16	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	_	14.5	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	30.6	_	nC	V _{DS} = -30V. I _D = -5A	
Gate-Source Charge	Q_{gs}	_	4.9	_	nC	V _{DS} = -30V, I _D = -3A	
Gate-Drain Charge	Q_{gd}	_	5.2	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.3	_	ns		
Turn-On Rise Time	t _R	_	15.4	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	79.2	_	ns	$R_G = 3\Omega$, $I_D = -5A$	
Turn-Off Fall Time	t _F	_	45.3	_	ns	1	
Body Diode Reverse Recovery Time	t _{RR}	_	15.2	_	ns	I _F = -5A, di/dt = -100A/μs	
Body Diode Reverse Recovery Charge	Q_{RR}	_	9.3	_	nC	I _F = -5A, di/dt = -100A/μs	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.





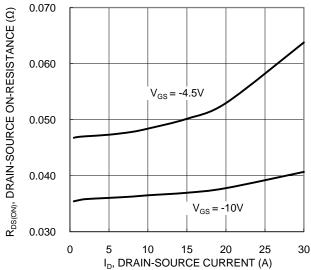


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

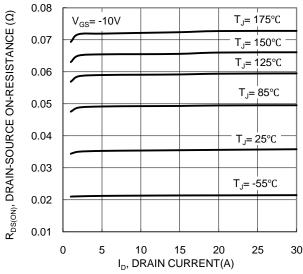


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

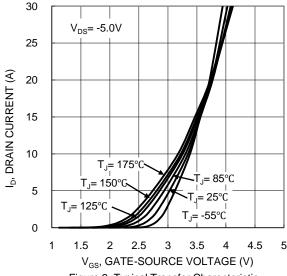
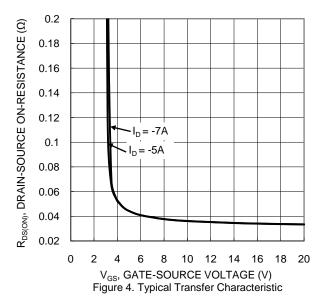


Figure 2. Typical Transfer Characteristic



2.2 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2 $V_{GS} = -10V, I_{D} = -7.0A$ 1.8 1.6 1.4 1.2 $V_{GS} = -4.5V, I_{D} = -7.0A$ 1 0.8 0.6 0.4 -25 0 25 50 75 100 125 150 175 T₁, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



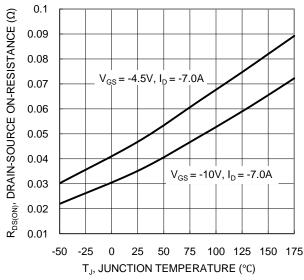


Figure 7. On-Resistance Variation with Temperature

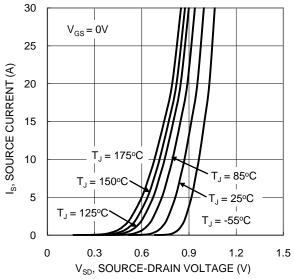


Figure 9. Diode Forward Voltage vs. Current

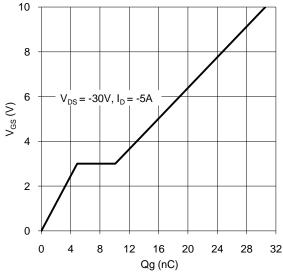


Figure 11. Gate Charge

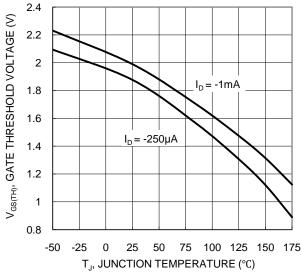
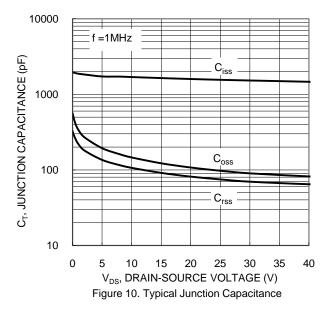
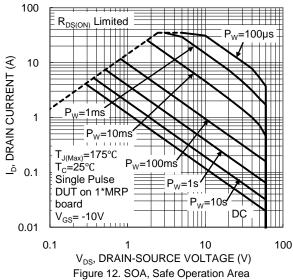


Figure 8. Gate Threshold Variation vs Temperature







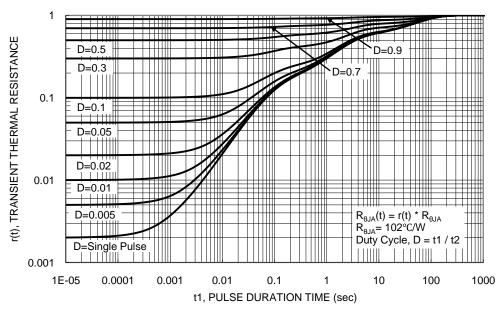


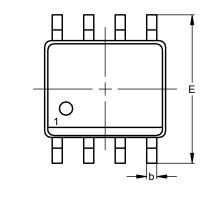
Figure 13. Transient Thermal Resistance

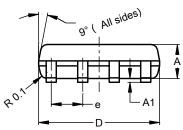


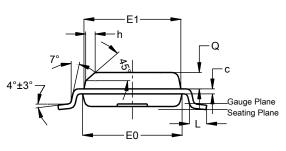
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





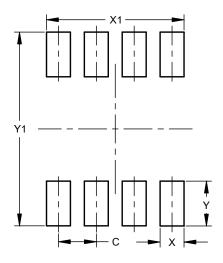


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A 1	0.10	0.20	0.15		
p	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
e 1.2			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Ø	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)			
C	1.27			
Х	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



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